

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D \text{ max}$ $T_A = 25^\circ\text{C}$
30V	14m Ω @ $V_{GS} = 10\text{V}$	8.0A
	20m Ω @ $V_{GS} = 4.5\text{V}$	6.7A

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

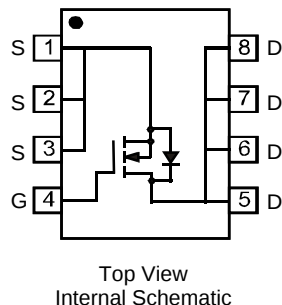
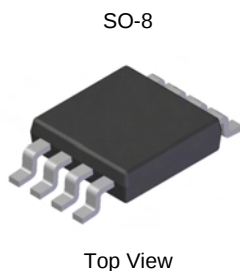
- DC-DC Converters
- Power management functions

Features and Benefits

- 14m Ω @ $V_{GS} = 10\text{V}$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.072 grams (approximate)

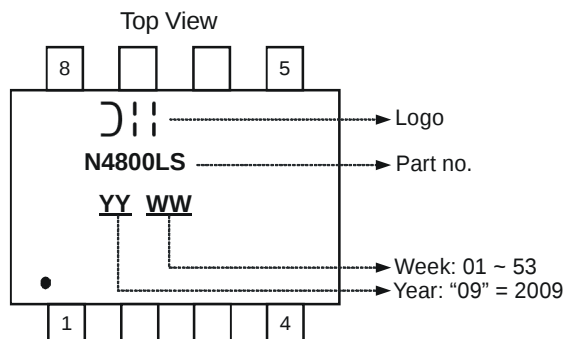


Ordering Information (Note 3)

Part Number	Case	Packaging
DMN4800LSSL-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 4) V _{GS} = 10V	I _D	8.0	A
Steady State T _A = 25°C		6.4	
Drain Current (Note 4) V _{GS} = 10V	I _D	6.7	A
Steady State T _A = 70°C		5.3	
Pulsed Drain Current (Note 5)	I _{DM}	50	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 4)	P _D	1.46	W
Thermal Resistance, Junction to Ambient	R _{θJA}	86	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	0.8	1.2	1.6	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	11 14	14 20	mΩ	V _{GS} = 10V, I _D = 8A V _{GS} = 4.5V, I _D = 7A
Forward Transconductance	g _{fs}	—	8	—	S	V _{DS} = 10V, I _D = 8A
Diode Forward Voltage (Note 6)	V _{SD}	—	0.72	0.94	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	798	—	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	128	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	122	—	pF	
Gate Resistance	R _G	—	1.37	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	—	8.7	—	nC	V _{GS} = 5V, V _{DS} = 15V, I _D = 9A
Gate-Source Charge	Q _{gs}	—	1.7	—		
Gate-Drain Charge	Q _{gd}	—	2.4	—		
Turn-On Delay Time	t _{d(on)}	—	5.03	—	ns	V _{DD} = 15V, V _{GEN} = 10V, R _L = 15Ω, R _G = 6.0Ω, I _D = 1A
Rise Time	t _r	—	4.50	—		
Turn-Off Delay Time	t _{d(off)}	—	26.33	—		
Fall Time	t _f	—	8.55	—		

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Repetitive rating, pulse width limited by junction temperature.
 - Short duration pulse test used to minimize self-heating effect.

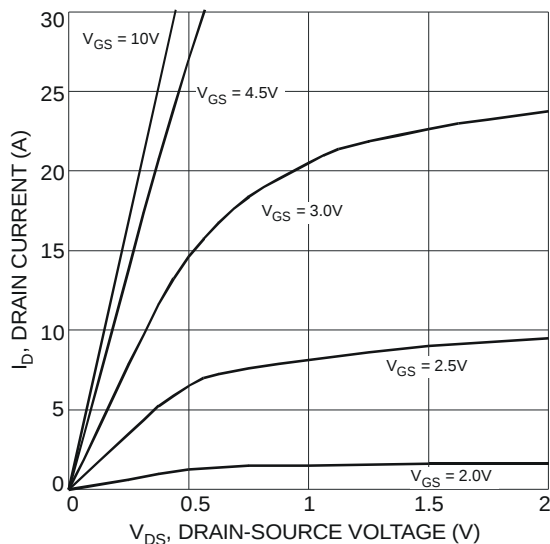


Fig. 1 Typical Output Characteristic

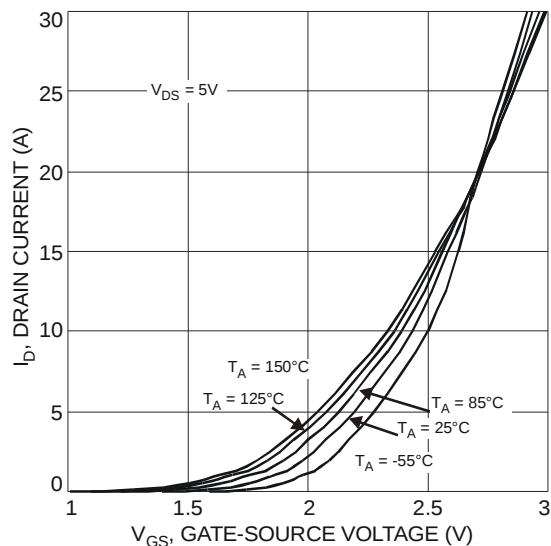


Fig. 2 Typical Transfer Characteristic

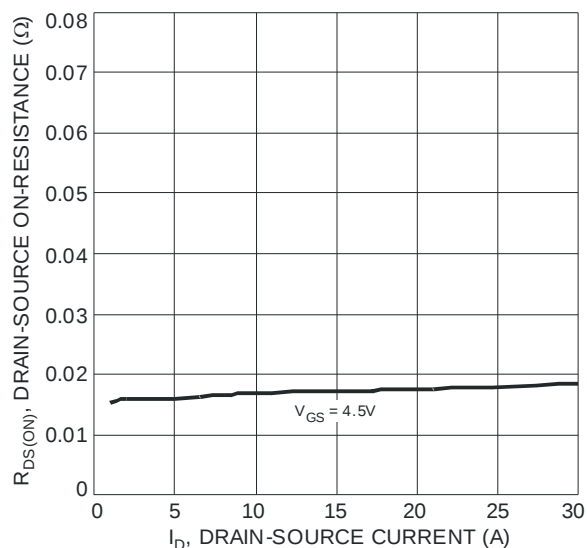


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

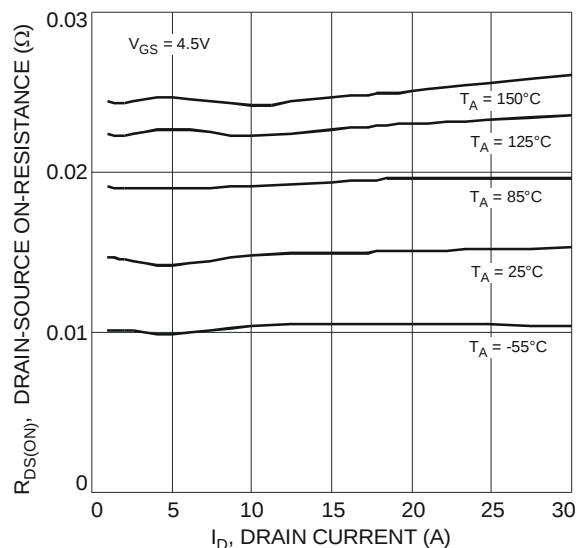


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

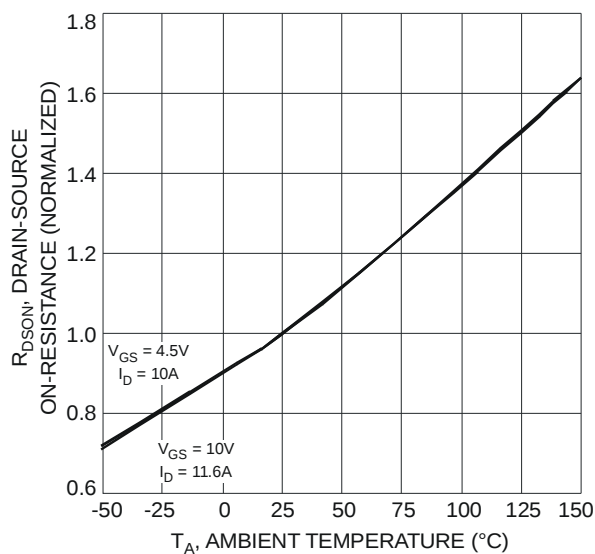


Fig. 5 On-Resistance Variation with Temperature

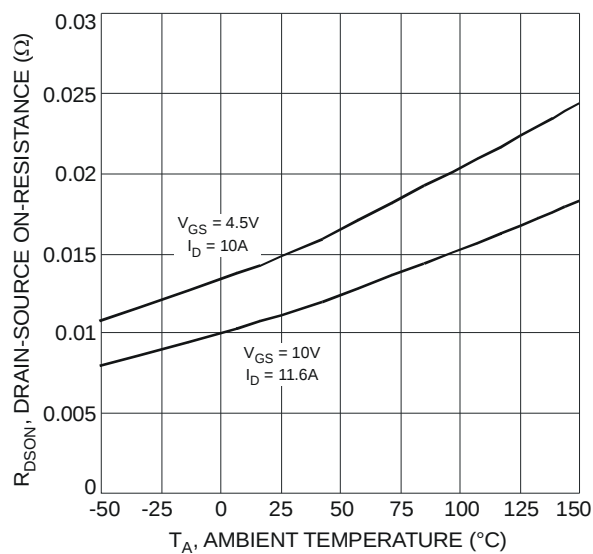


Fig. 6 On-Resistance Variation with Temperature

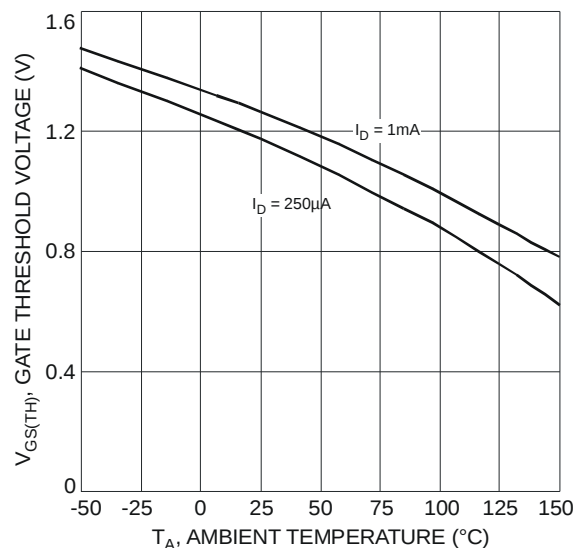


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

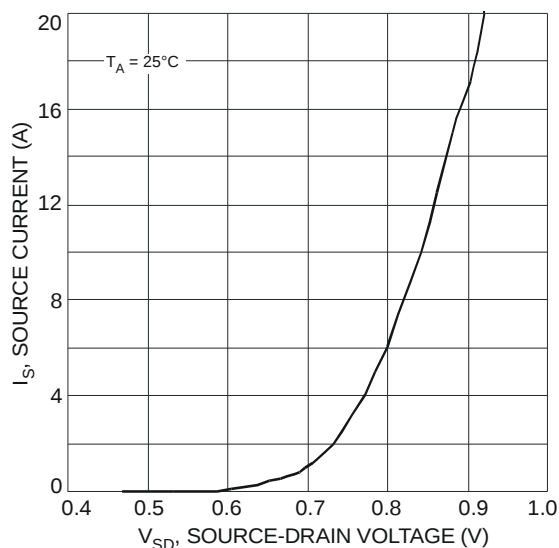


Fig. 8 Diode Forward Voltage vs. Current

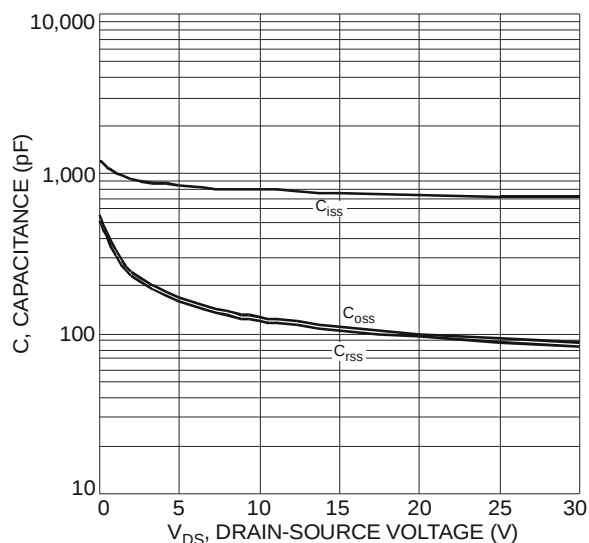


Fig. 9 Typical Total Capacitance

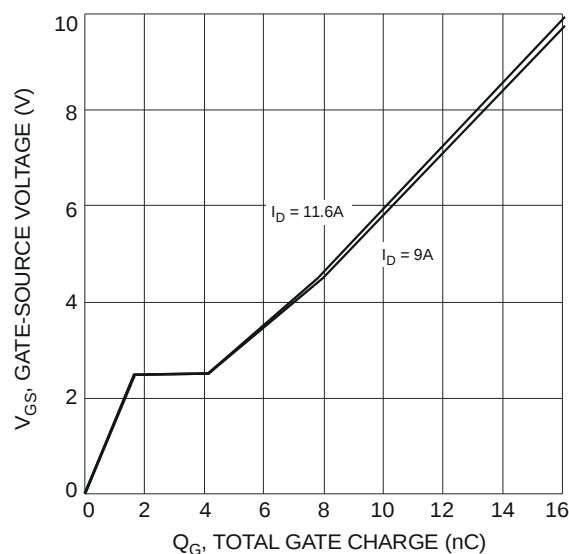


Fig. 10 Total Gate Charge

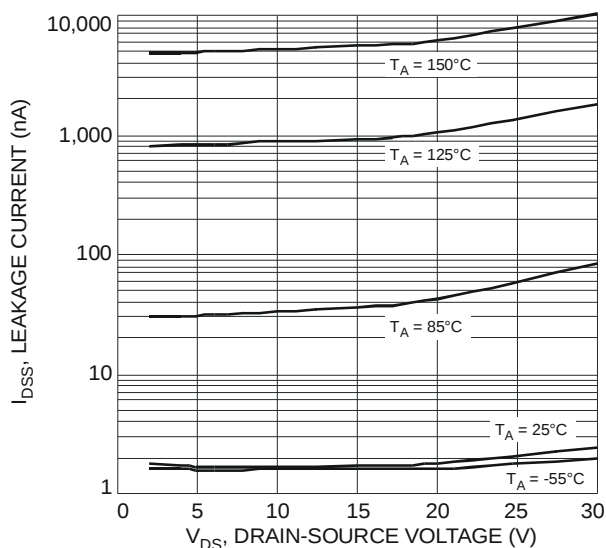


Fig. 11 Typical Leakage Current vs. Drain-Source Voltage

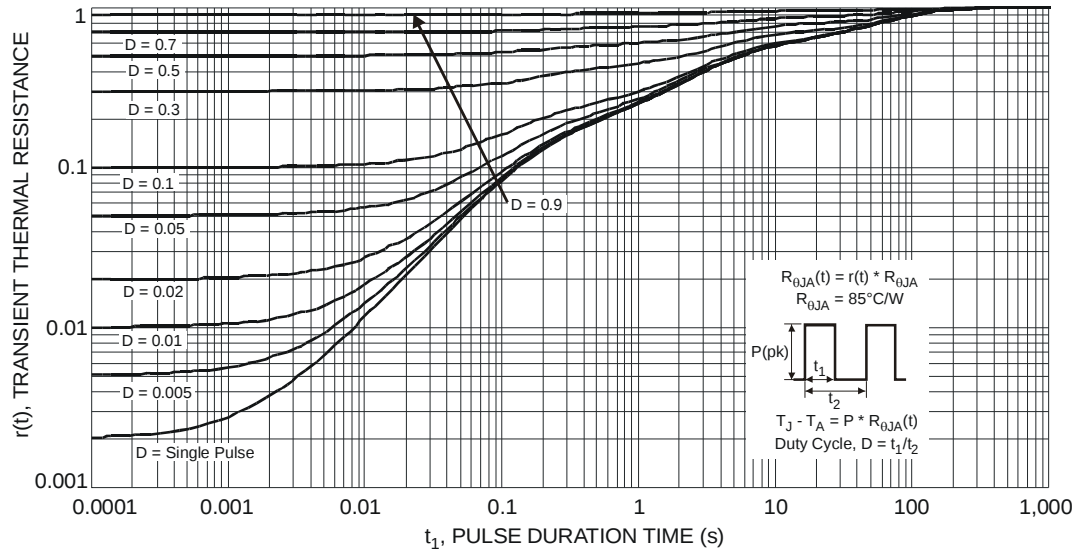
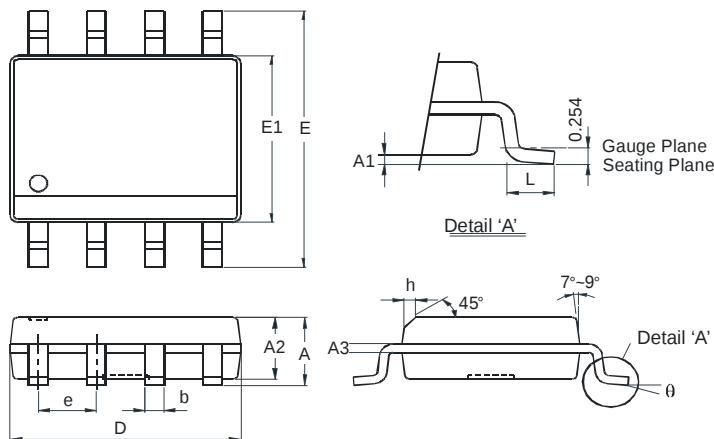


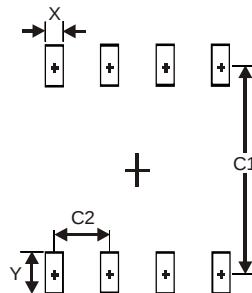
Fig. 12 Transient Thermal Response

Package Outline Dimensions



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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